## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant:

Yang, et al.

Attorney Docket:

TSM03-0929

Filed:

Herewith

Examiner:

**TBD** 

Serial No.:

**TBD** 

Art Unit:

TBD

For:

Methods and Structures for Planar and Multiple-Gate Transistors Formed on SOI

Mail Stop: Patent Application Commissioner for Patents P. O. Box 1450 Alexandria, VA 22313-1450

## **INFORMATION DISCLOSURE STATEMENT**

The Applicant wishes to bring to the attention of the Patent and Trademark Office the information noted on the enclosed form PTO/SB/08A & B that may be considered material to the examination of the above-identified application.

No fee is due at this time, as this Information Disclosure Statement is being filed concurrently with the patent application.

Pursuant to 37 CFR 1.98(a)(2)(i), as amended, copies of U.S. Patents cited are not being submitted. However, Applicant has included copies of any non-patent literature.

Respectfully submitted,

April 13, 2004

Date

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Sheet	1	of	1	Attorney Docket Number	TSM03-0929	

U.S. PATENT DOCUMENTS						
Examiner Initials*	Cite No.1	Document Number  Number - Kind Code <sup>2 (# known)</sup>	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	
	ļ	US-6,222,234 B1	04-24-2001	lmai		
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		FOREIGI	N PATENT DOCU	JMENTS		
Examiner Initials*	Cite No.1	Foreign Patent Document  Country Code <sup>3</sup> - Number <sup>4</sup> - Kind Code <sup>5</sup> ( <i>if known</i> )	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	τ°
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NON PATENT LITERATURE DOCUMENTS					
Examiner Initials*	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>		
	i	CHAU, R., et al., "A 50nm Depleted-Substrate CMOS Transistor (DST)," IEDM (2001) pp. 621-624.			
		SHAHIDI, G.G., "SOI Technology for the GHz Era," IBM J. RES. & DEV., Vol. 46, No. 2/3 (March/May 2002) pp. 121-131.			
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Signature	Date	
Olgitature	Considered	

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. 'Applicant's unique citation designation number (optional). 'See Kinds Codes of USPTO Patent Documents at <a href="https://www.uspto.gov">www.uspto.gov</a> or MPEP 901.04. 'Senter Office that issued the document, by the two-letter code (WIPO Standard ST.3). 'For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. 'Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. 'Applicant is to place a check mark here if English language

Translation is attached.

This collection of information is required by 37 CFR 1.97 and 1.98. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 2 hours to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.